L Number	Hits	Search Text	DB	Time stamp
4	1301	(365/194).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:19
5	347	(365/204).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:19
6	2122	(365/149).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:19
7	189	(365/150).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:19
8	938	(365/210).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:20
9	1	"diffusion replica circuit"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:20
10	48	terzioglu.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:20
11	121	afghahi.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:21
12	3165	"dummy cell"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:21
14	788	"dummy cell" same (capacitance capacity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:22
15	454	("dummy cell" same (capacitance capacity)) same (bitline "bit line")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:23
16	670	"dummy bit line"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:23
17	140	"dummy bit line" same (capacitance capacity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:24
18	50	("dummy bit line" same (capacitance capacity)) same transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:24

19	209	(("dummy cell" same (capacitance capacity)) same (bitline "bit line")) same transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:24
20	125	((("dummy cell" same (capacitance capacity)) same (bitline "bit line")) same transistor) same capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:24
-	0	("9776029").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/04 14:19
-	6	"09/776,029"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:19